



ELECTRONICS, INC.
 44 FARRAND STREET
 BLOOMFIELD, NJ 07003
 (973) 748-5089
<http://www.nteinc.com>

NTE5576 & NTE5578 Silicon Controlled Rectifier (SCR) 175 Amps, TO94

Absolute Maximum Ratings: ($T_J = +125^\circ\text{C}$ unless otherwise specified)

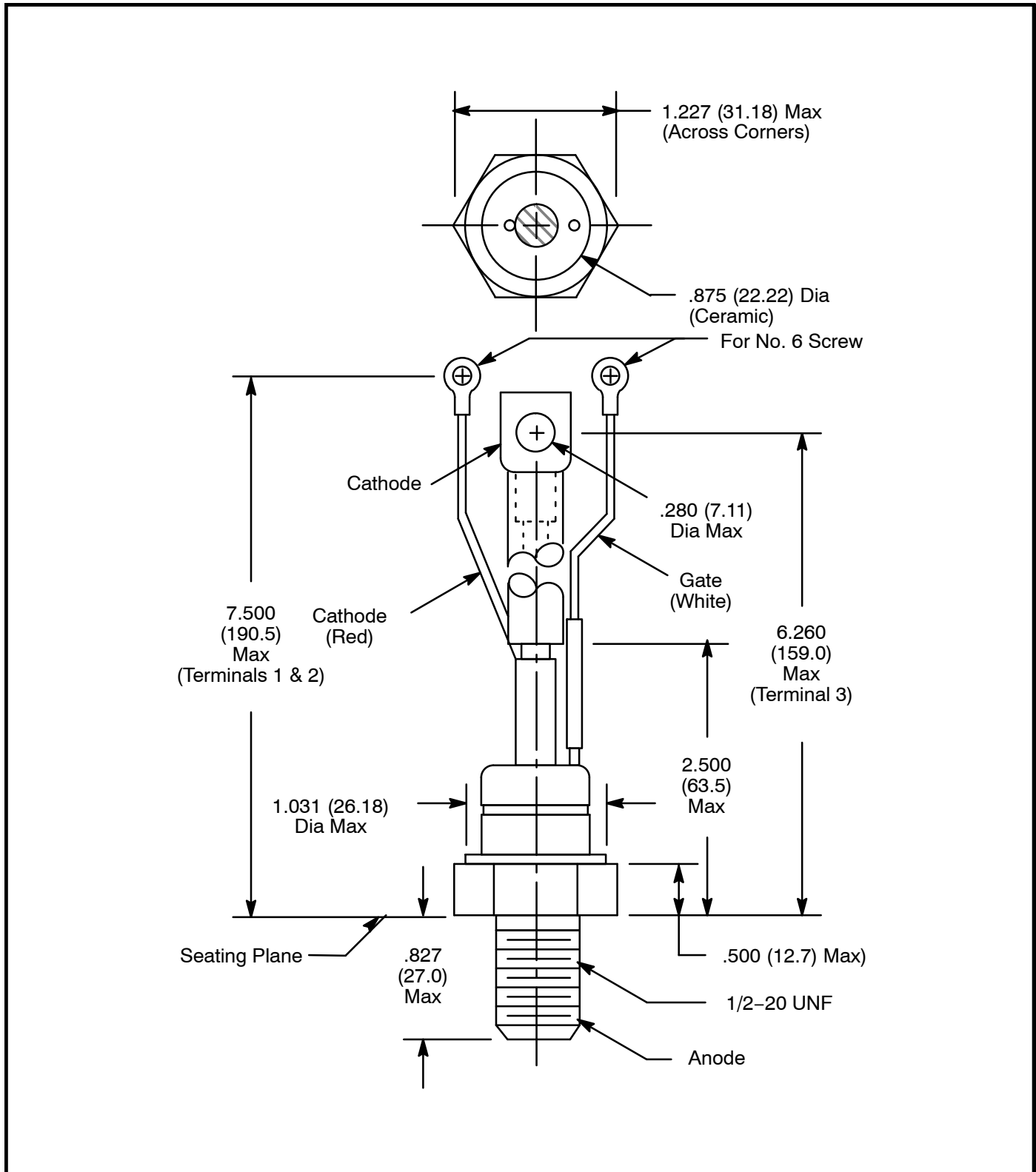
Repetitive Peak Voltages, V_{DRM} & V_{RRM}	
NTE5576	600V
NTE5578	1600V
Non-Repetitive Peak Off-State Voltage, V_{DSM}	
NTE5576	600V
NTE5578	1600V
Non-Repetitive Peak Reverse Blocking Voltage, V_{RSM}	
NTE5576	700V
NTE5578	1700V
Average On-State Current (Half Sine Wave, $T_C = +90^\circ\text{C}$), $I_{T(AV)}$	
	110A
RMS On-State Current, $I_{(RMS)}$	
	175A
Continuous On-State Current, I_T	
	175A
Peak One-Cycle, Non-Repetitive Surge Current (10ms Duration), I_{TSM}	
60% V_{RRM} reapplied	2450A
$V_R \leq 10V$	2695A
Maximum I^2t for Fusing ($V_R \leq 10V$), I^2t	
10ms Duration	36300A ² sec
10ms Duration	27000A ² sec
Peak Forward Gate Current (Anode Positive with Respect to Cathode), I_{FGM}	
	19A
Peak Forward Gate Voltage (Anode Positive with Respect to Cathode), V_{FGM}	
	18V
Peak Reverse Gate Voltage, V_{RGM}	
	5V
Average Gate Power, P_G	
	2W
Peak Gate Power (100 μ s Pulse Width), P_{GM}	
	100W
Rate of Rise of Off-State Voltage (To 80% V_{DRM} , Gate Open), dv/dt	
	200V/ μ s
Rate of Rise of ON-State Current, di/dt	
(Gate Drive 20V, 20 Ω , with $t_r \leq 1\mu$ s, Anode Voltage $\leq 80\%$ V_{DRM})	
Repetitive	500A/ μ s
Non-Repetitive	1000A/ μ s

Electrical Characteristics: (Maximum values @ $T_J = +125^\circ\text{C}$ unless otherwise specified)

Peak On-State Voltage ($I_{TM} = 377A$), V_{TM}	1.57V
Forward Conduction Threshold Voltage, V_O	0.9V
Forward Conduction Slope Resistance, r	1.79m Ω
Repetitive Peak Off-State Current (At V_{DRM}), I_{DRM}	20mA
Repetitive Peak Reverse Current (At V_{RRM}), I_{RRM}	20mA
Maximum Gate Current Required to Fire All Devices ($V_A = 6V$, $I_A = 2A$, $T_J = +25^\circ\text{C}$), I_{GT} ..	150mA
Maximum Gate Voltage Required to Fire All Devices ($V_A = 6V$, $I_A = 2A$, $T_J = +25^\circ\text{C}$), V_{GT}	3V
Maximum Holding ($V_A = 6V$, $I_A = 2A$, $T_J = +25^\circ\text{C}$), I_H	600mA

Electrical Characteristics (Cont'd): (Maximum values @ $T_J = +125^\circ\text{C}$ unless otherwise specified)

Maximum Gate Voltage which will not Trigger any Device, V_{GD}	0.25V
Operating Temperature Range, T_C	-40° to $+125^\circ\text{C}$
Storage Temperature Range, T_{stg}	-40° to $+150^\circ\text{C}$
Thermal Resistance, Junction-to-Case ($V_F = \text{Max Rating}$), R_{thJC}	
DC and 180° Sine wave	0.23°C/W
120° Rectangular wave	0.28°C/W
Thermal Resistance, Case-to-Heat Sink, R_{thC-HS}	0.08°C/W



X-ON Electronics

Largest Supplier of Electrical and Electronic Components

Click to view similar products for [SCRs](#) category:

Click to view products by [NTE](#) manufacturer:

Other Similar products are found below :

[NTE5428](#) [NTE5448](#) [NTE5457](#) [NTE5511](#) [T1500N16TOF VT](#) [T720N18TOF](#) [T880N14TOF](#) [T880N16TOF](#) [TN1205H-6G](#) [TN1215-800B-TR](#)
[TS110-7UF](#) [TT104N12KOF-A](#) [TT104N12KOF-K](#) [TT162N16KOF-A](#) [TT162N16KOF-K](#) [TT330N16AOF](#) [VS-111RKI120PBF](#) [VS-16RIA100](#)
[VS-22RIA20](#) [VS-2N5206](#) [VS-2N685](#) [VS-40TPS08A-M3](#) [VS-50RIA10](#) [057219R](#) [T1190N16TOF VT](#) [T1220N22TOF VT](#) [T201N70TOH](#)
[T830N14TOF](#) [T830N18TOF](#) [TD92N16KOF-A](#) [TT250N12KOF-K](#) [VS-ST180S12P0V](#) [VS-25RIA40](#) [VS-16RIA120](#) [VS-30TPS08PBF](#)
[TN1215-800G-TR](#) [NTE5427](#) [NTE5442](#) [X0405NF 1AA2](#) [VS-ST300S20P0PBF](#) [T2160N28TOF VT](#) [TT251N16KOF-K](#) [VS-22RIA100](#) [VS-](#)
[16RIA40](#) [CR02AM-8#F00](#) [VS-ST110S12P0VPBF](#) [TD250N16KOF-A](#) [GA301A](#) [VS-ST110S16P0](#) [VS-10RIA10](#)